RST013N04SDB8

N-MOSFET PDFN5*6 40V,217A,1.3mΩ

Features

- Uses advanced SGT technology
- Extremely low on-resistance R_{DS}(on)
- Excellent gate charge x R_{DS}(on) product(FOM)

Application

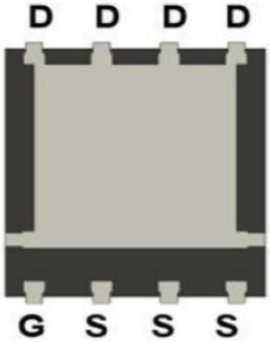
- Motor control and drive
- Battery management
- DC/DC

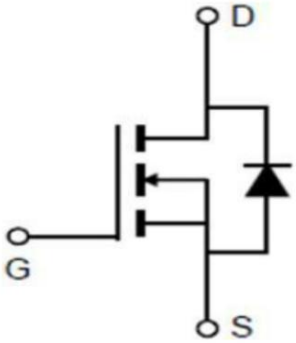
Product Summary

Package	PDFN5*6
V_{DS}	40V
$R_{DS(on)@VGS=10V}$	1.3mΩ
I_D	217A

Package Marking







Type	Package	Marking	Reel Size	Tape Width	Packing	Qty
RST013N04SDB8	PDFN5*6	LR013N04SDB8	330*16.5mm	12mm	Reel&Tape	5000

Maximum Ratings (TC=25℃unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous drain current T_c=25℃（Silicon limit） T_c=100℃（Silicon limit）	I_D	 217 138	A
Pulsed Drain Current	I_{DM}	960	A
Maximum Power Dissipation	P_d	125	W
Single pulse avalanche energy	E_{AS}	1089	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R_{thJC}	1.0	℃/W
Thermal Resistance,Junction-to-Ambient	R_{thJA}	62	

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	min	typ	max	Unit
Static Characteristic						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	2.0	3.0	4.0	
Zero gate voltage drain current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate-source leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=30A,V_{GS}=10V	-	1.3	1.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=100A	-	312	-	S
Dynamic Characteristic						
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V, f=1MHz	-	6982	-	pF
Output Capacitance	C_{oss}		-	1625	-	
Reverse Transfer Capacitance	C_{rss}		-	43	-	
Gate resistance	Rg	f=1MHz	-	2.3	-	Ω
Gate Total Charge	Q_G	V_{DS}=20V,I_D=20A, V_{GS}=10V	-	112	-	nC
Gate-Source charge	Q_{gs}		-	41	-	
Gate-Drain charge	Q_{gd}		-	19	-	
Turn-on delay time	$t_{d(on)}$	V_{GS}=10V, V_{DS}=20V, R_G=1.6Ω	-	32	-	ns
Rise time	t_r		-	65	-	
Turn-off delay time	$t_{d(off)}$		-	75	-	
Fall time	t_f		-	40	-	

Body Diode Characteristic

Diode Forward Voltage	V_{SD}	V_{GS}=0V,IS=20A	-	-	1.2	v
Reverse Recovery Time	t_{rr}	I_F =20A di/dt = 100A/μs	-	68	-	ns
Reverse Recovery Charge	Q_{rr}		-	120	-	nC

Typical Performance Characteristics

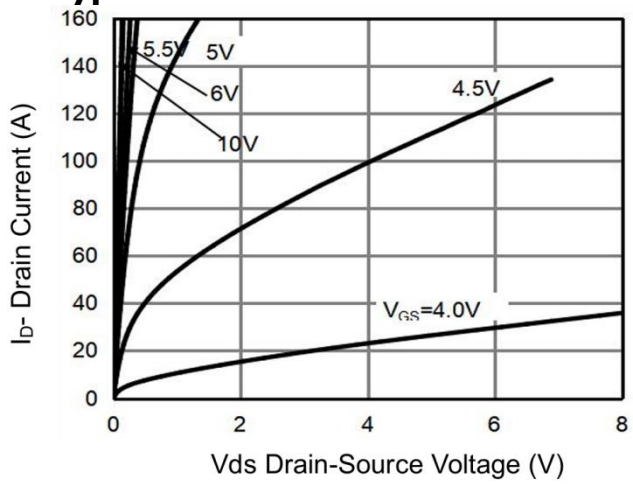


Figure 1 Output Characteristics

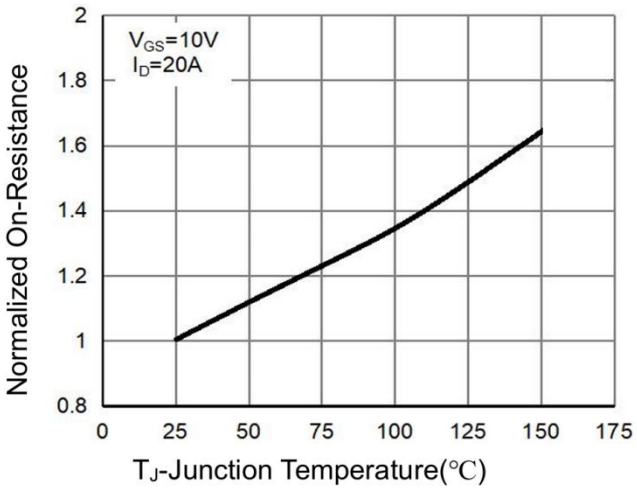


Figure 4 Rdson-Junction Temperature

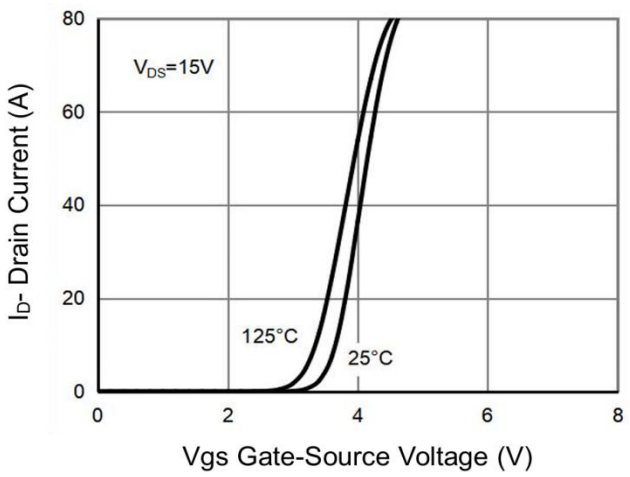


Figure 2 Transfer Characteristics

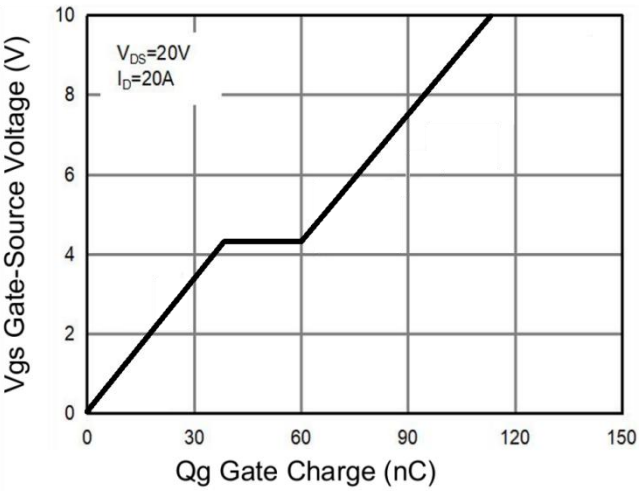


Figure 5 Gate Charge

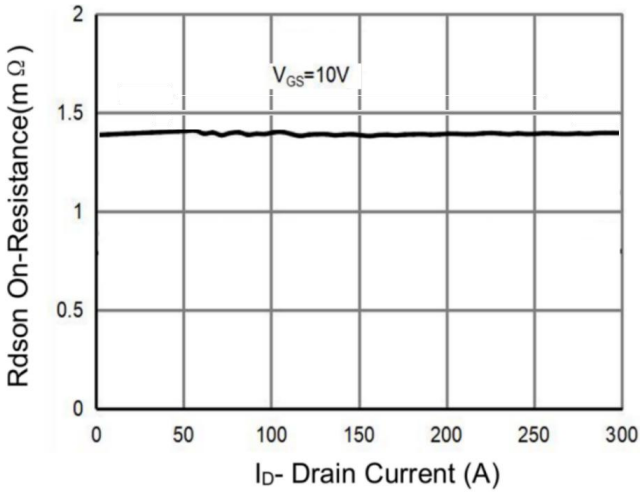


Figure 3 Rdson- Drain Current

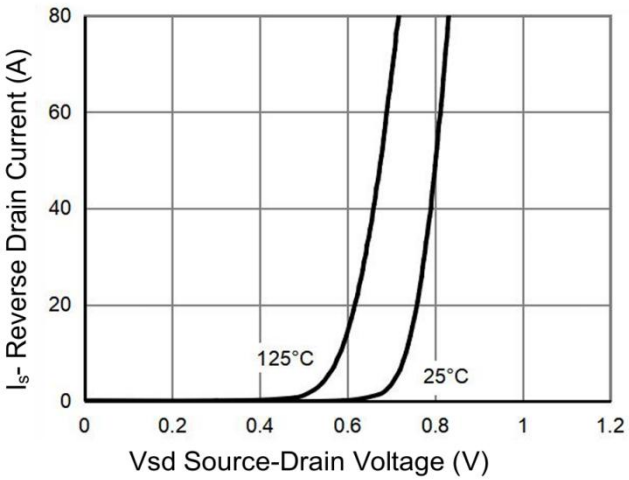


Figure 6 Source- Drain Diode Forward

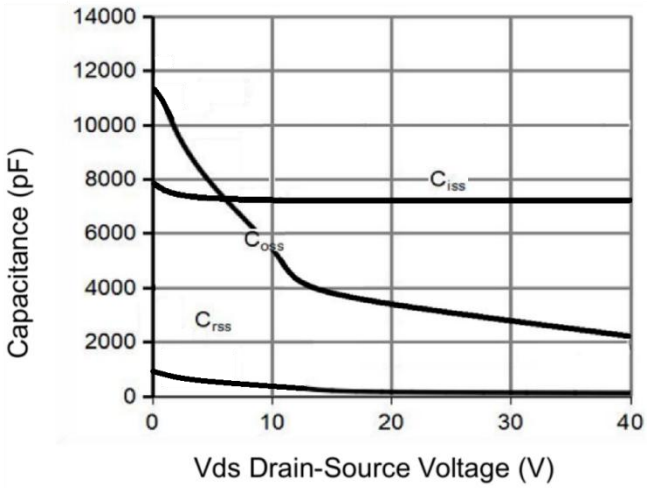


Figure 7 Capacitance vs Vds

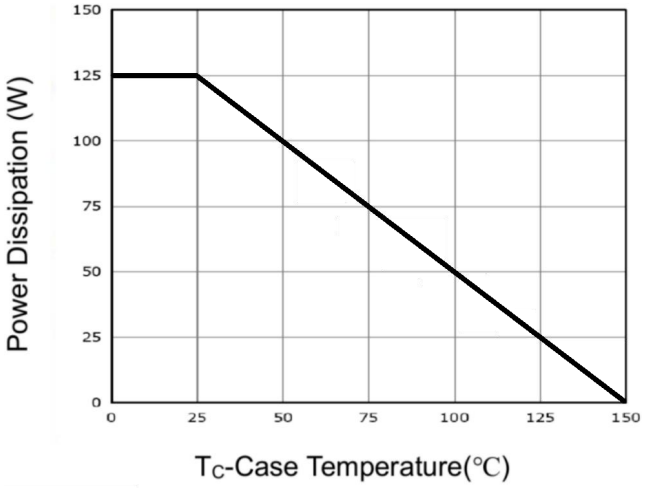


Figure 9 Power De-rating

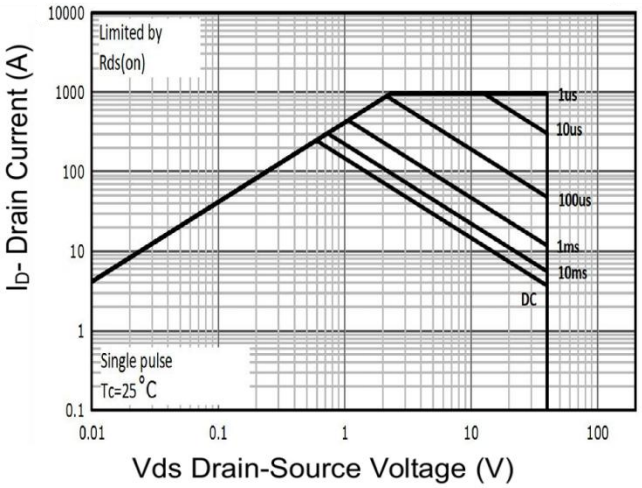


Figure 8 Safe Operation Area

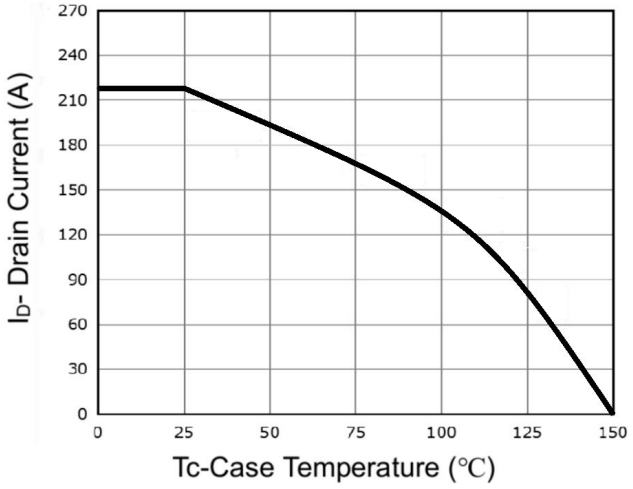


Figure 10 Current De-rating

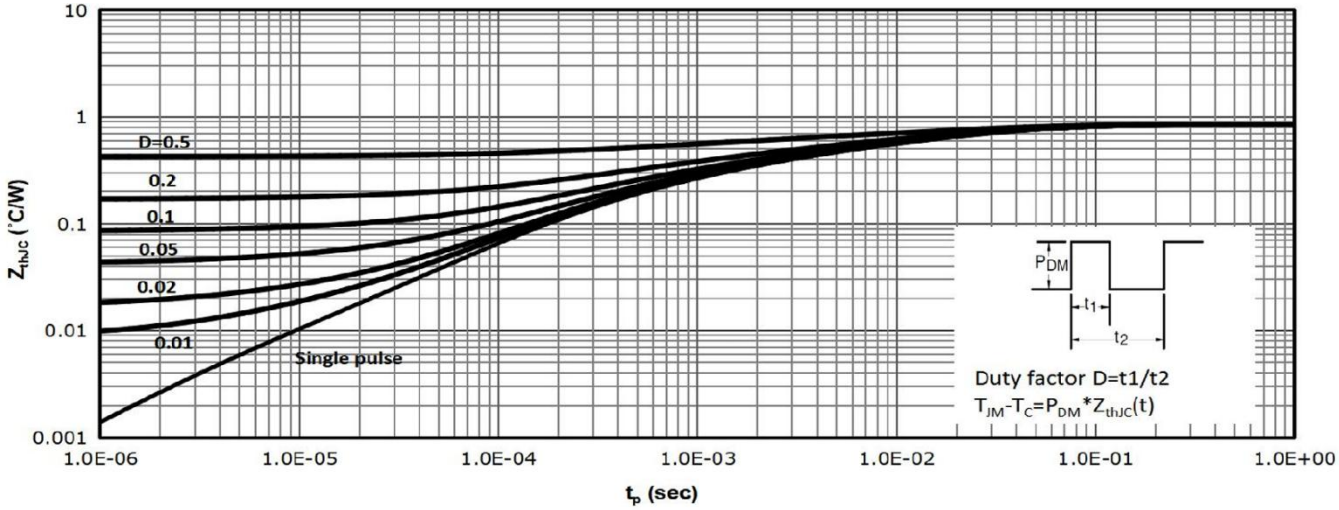
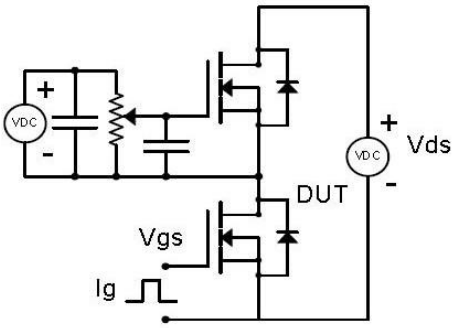
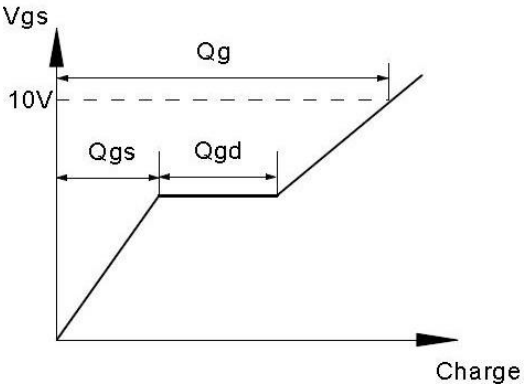


Figure 11 Maximum Transient Thermal Impedance

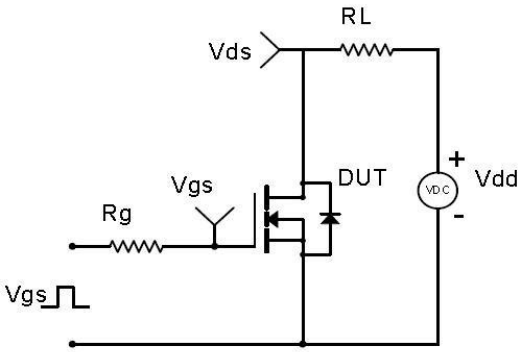
Test Circuit & Waveform

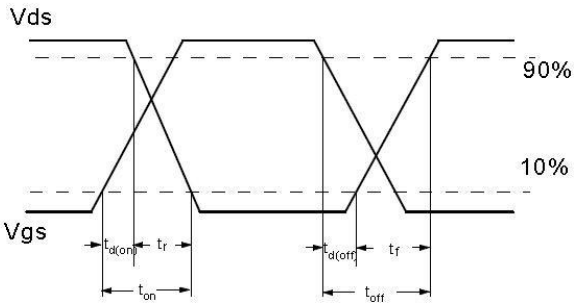
Gate Charge Test Circuit & Waveform



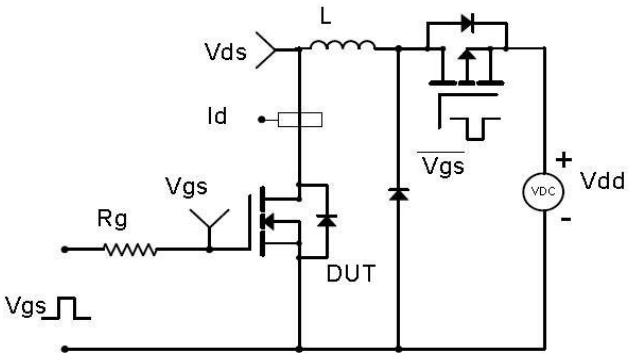


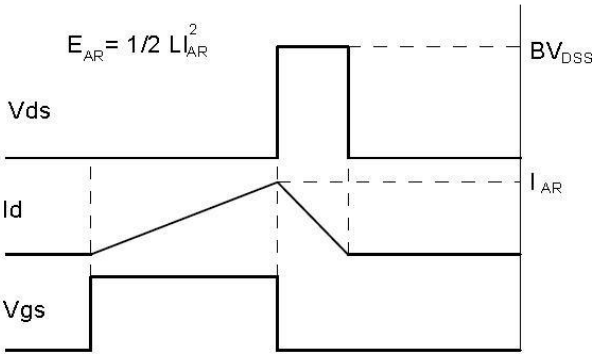
Resistive Switching Test Circuit & Waveforms



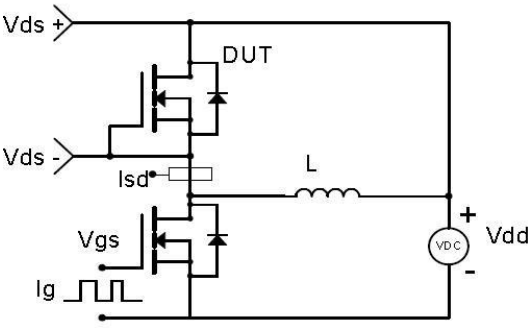


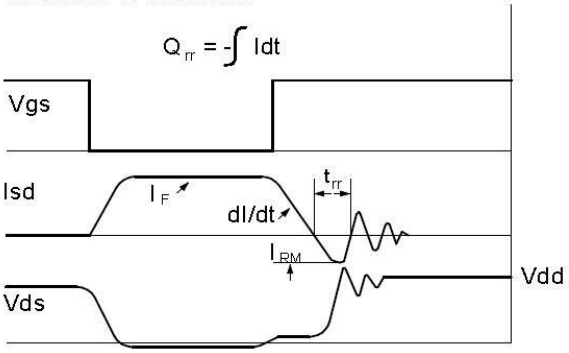
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



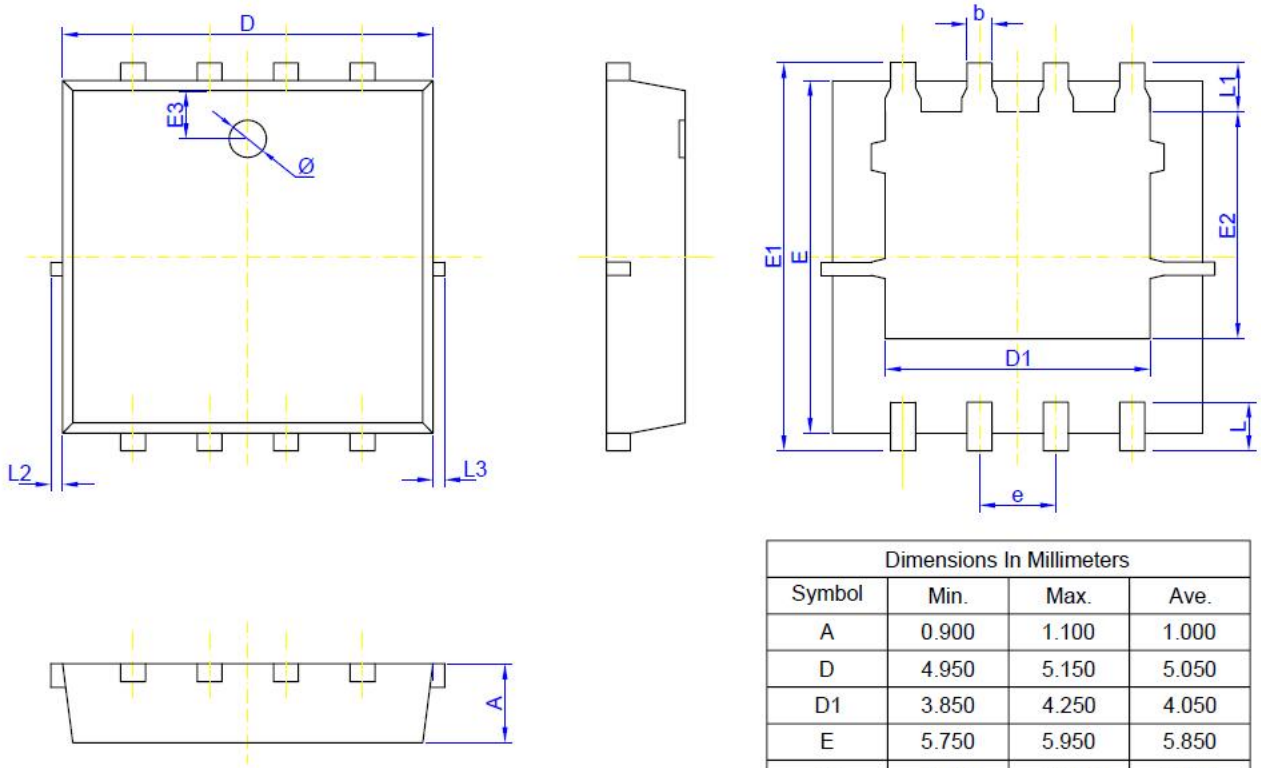


Diode Recovery Test Circuit & Waveforms





Package Outline:PDFN5*6



Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.900	1.100	1.000
D	4.950	5.150	5.050
D1	3.850	4.250	4.050
E	5.750	5.950	5.850
E1	5.950	6.350	6.150
E2	3.300	3.700	3.500
E3	0.900	1.300	1.100
b	0.250	0.350	0.300
e	1.220	1.320	1.270
L	0.585	0.785	0.685
L1	0.525	0.725	0.625
Ø	1.000	1.400	1.200
L2	0~0.100		
L3	0~0.100		

注：
1.未注公差±0.05,未标注圆角Rmax=0.25
2.标注单位mm

Revision History:

Revision	Date	Major changes
1.0	2026/3/2	Release of Preliminary version.
2.0	2026/4/23	Update Ron and ID.